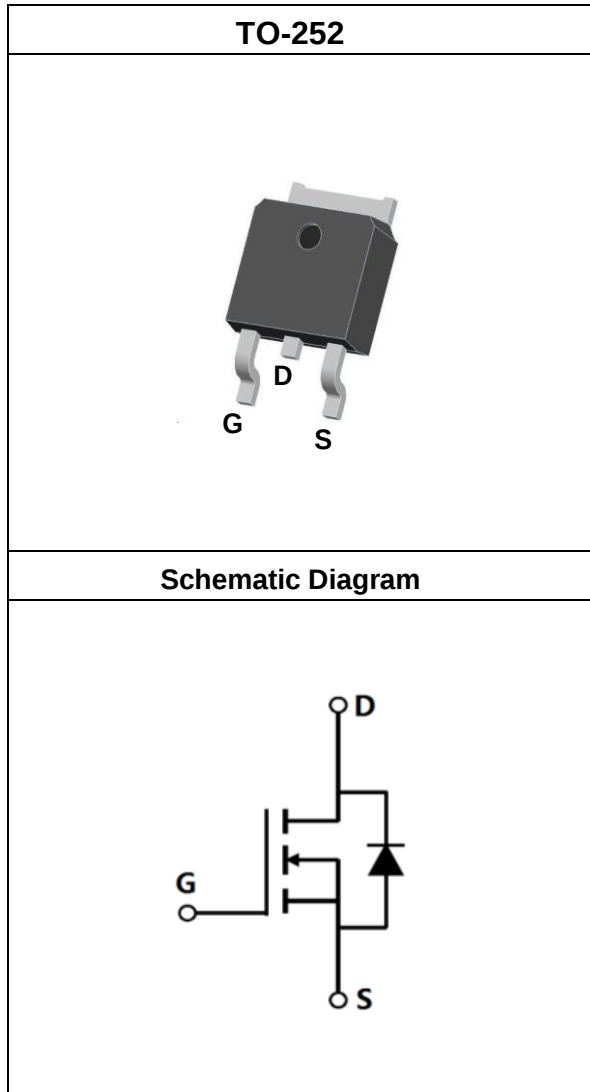


N-channel 80V, 6.5mΩ max., 85A
 SGT MOSFET S2 in TO-252

Datasheet – Production data

1. Descriptions



Key Performance Parameters

Parameters	Value	Unit
BV_{DSS}	80	V
$R_{DS(on),max}$	6.5	mΩ
$Q_{g,type}$	33.9	nC
$I_{D,pulse}$	300	A
E_{AS}	225	mJ

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$.
- High-speed switching.
- Qualified for industrial grade applications according to JEDEC.
- 100% UIS Tested.

Applications

High-Efficiency DC-DC Converters, High-Frequency Switching and Synchronous Rectification, Motor Drivers.

Type/Ordering Code	Package	Marking	Related Links
CSD065N08S2	TO-252	065N08S2	see Appendix A

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2. Maximum Ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 1. Absolute Maximum Ratings

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
V_{DS}	Drain-source voltage ¹⁾	-	-	80	V	$V_{GS}=0V$, $I_D=250\mu A$
I_D	Continuous drain current (Silicon Limited)	-	-	85 60	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
$I_{D,pulse}$	Pulsed drain current	-	-	300	A	$T_C=25^\circ\text{C}$
E_{AS}	Avalanche energy, single pulse ²⁾	-	-	225	mJ	$I_D=30A$; $V_{DD}=50V$
I_{AS}	Avalanche current	-	-	30	A	-
V_{GS}	Gate source voltage	-20	-	20	V	static; AC ($f>1\text{ Hz}$)
P_{tot}	Power dissipation	-	-	100	W	$T_C=25^\circ\text{C}$
T_j, T_{stg}	Operating and storage temperature	-55	-	150	$^\circ\text{C}$	-
I_S	Continuous diode forward current	-	-	85	A	$T_C=25^\circ\text{C}$
$I_{S,pulse}$	Diode pulse current ²⁾	-	-	300	A	$T_C=25^\circ\text{C}$

1) Limited by T_j max. Maximum duty cycle $D=0.75$.

2) $V_{DD}=50V$, $L=0.5mH$, $R_G=25\Omega$, Starting $T_j=25^\circ\text{C}$.

3. Thermal Characteristics

Table 2. Thermal Characteristics

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
R_{thJC}	Thermal resistance, junction - case	-	-	1.5	°C/W	$T_C = 25^{\circ}\text{C}$
R_{thJA}	Thermal resistance, junction - ambient	-	-	65	°C/W	$T_C = 25^{\circ}\text{C}$
T_{sold}	Soldering temperature, wavesoldering only allowed at leads	-	-	260	°C	Lead Temperature (Soldering, 10 sec)

4. Electrical Characteristics

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 3. Static Characteristics

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-source breakdown voltage	80	-	-	V	$V_{GS}=0V, I_D=250\mu A$
$V_{(GS)th}$	Gate threshold voltage	1.2	1.7	2.5	V	$V_{DS}=V_{GS}, I_D=250\mu A$
I_{DSS}	Zero gate voltage drain current	-	-	1	μA	$V_{DS}=80V, V_{GS}=0V, T_j=25^\circ C$
I_{GSS}	Gate-source leakage current	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
$R_{DS(on)}$	Drain-source on-state resistance	-	5.8	6.5	m Ω	$V_{GS}=10V, I_D=20A, T_j=25^\circ C$
R_G	Gate resistance	-	0.95	-	Ω	$V_{DD}=0V, V_{GS}=0V, F=1MHz$
g_{fs}	Transconductance		40		S	$V_{DS}=5V, I_D=20A$

Table 4. Dynamic Characteristics

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
C_{iss}	Input capacitance	-	2050	-	pF	$V_{GS}=0V, V_{DS}=40V, f=250kHz$
C_{oss}	Output capacitance	-	300	-	pF	$V_{GS}=0V, V_{DS}=40V, f=250kHz$
C_{rss}	Reverse transfer capacitance	-	13	-	pF	$V_{GS}=0V, V_{DS}=40V, f=250kHz$
$t_{d(on)}$	Turn-on delay time	-	15.4	-	ns	$V_{DD}=40V, V_{GS}=10V, I_D=20A, R_G=5\Omega$
t_r	Rise time	-	8.6	-	ns	$V_{DD}=40V, V_{GS}=10V, I_D=20A, R_G=5\Omega$
$t_{d(off)}$	Turn-off delay time	-	43.4	-	ns	$V_{DD}=40V, V_{GS}=10V, I_D=20A, R_G=5\Omega$
t_f	Fall time	-	12.7	-	ns	$V_{DD}=40V, V_{GS}=10V, I_D=20A, R_G=5\Omega$

Table 5. Gate Charge Characteristics

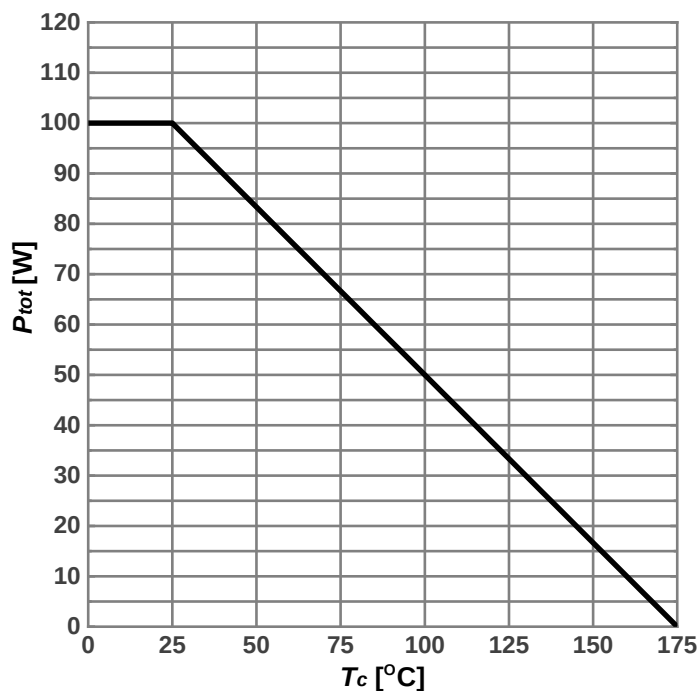
Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
Q_{gs}	Gate to source charge	-	5.9	-	nC	$V_{DD}=40V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Q_{gd}	Gate to drain charge	-	7.23	-	nC	$V_{DD}=40V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Q_g	Gate charge total	-	33.9	-	nC	$V_{DD}=40V, I_D=20A, V_{GS}=0 \text{ to } 10V$
$V_{plateau}$	Gate plateau voltage	-	3.2	-	V	$V_{DD}=40V, I_D=20A, V_{GS}=0 \text{ to } 10V$

Table 6. Reverse Diode Characteristics

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
V_{SD}	Diode forward voltage	-	0.85	-	V	$V_{GS}=0V, I_F=20A, T_j=25^\circ C$
t_{rr}	Reverse recovery time	-	30.2	-	ns	$V_R=40V, I_F=20A, di_F/dt=100A/\mu s$
Q_{rr}	Reverse recovery charge	-	28.3	-	nC	$V_R=40V, I_F=20A, di_F/dt=100A/\mu s$
I_{rrm}	Peak reverse recovery current	-	1.4	-	A	$V_R=40V, I_F=20A, di_F/dt=100A/\mu s$

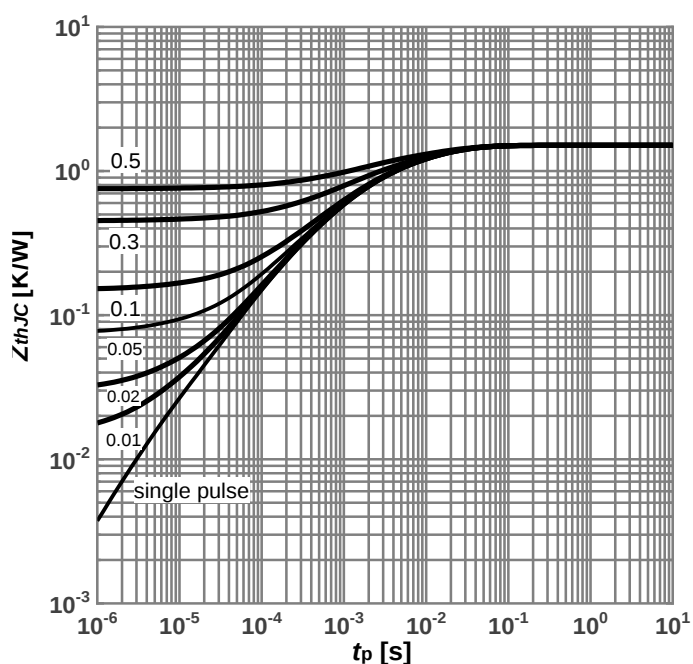
5. Electrical Characteristics Diagrams

Diagram 1: Power dissipation



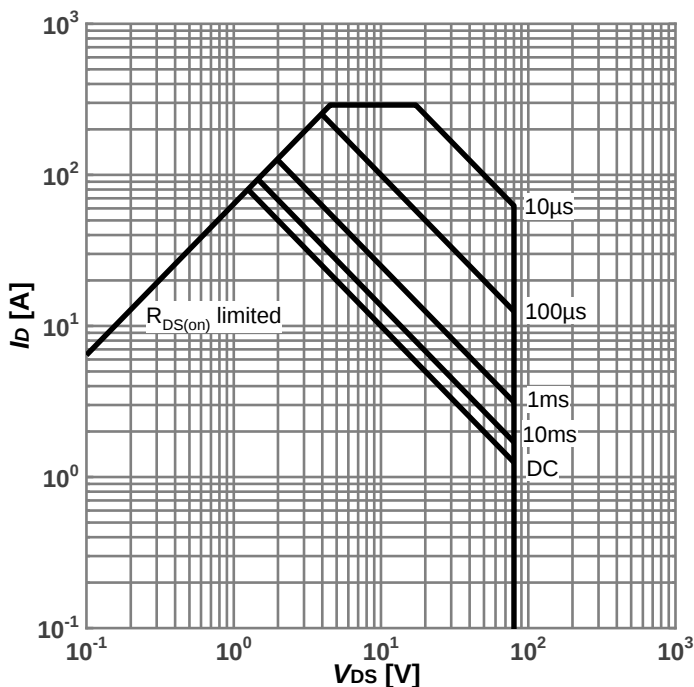
$$P_{tot}=f(T_c)$$

Diagram 2: Max. transient thermal impedance



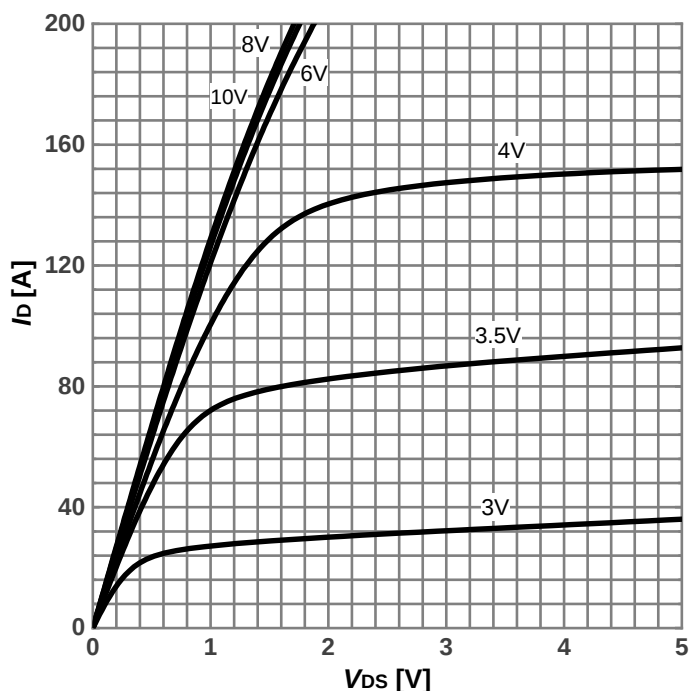
$$Z_{thJC}=f(t_p); \text{ parameter: } D= t_p/T$$

Diagram 3: Safe operating area



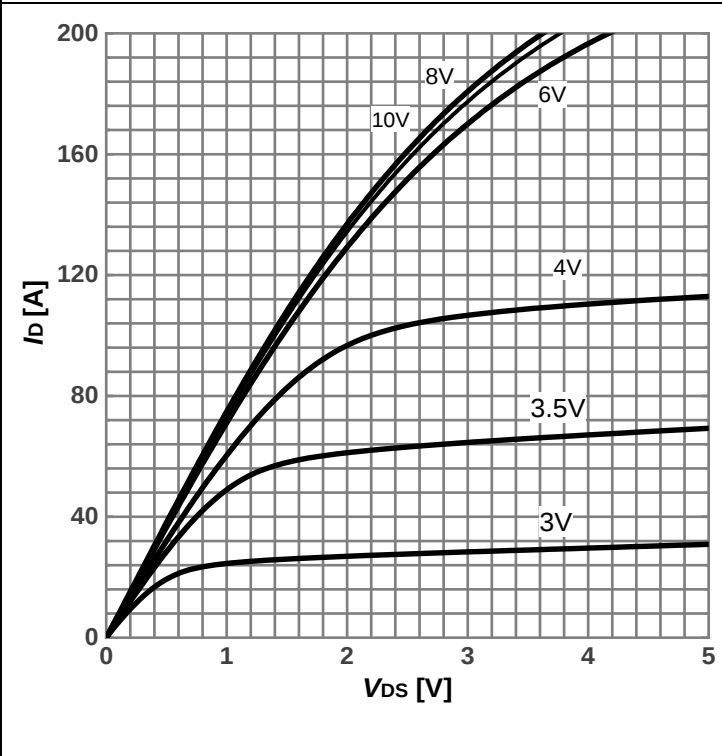
$$I_D=f(V_{DS}); T_J=25^{\circ}\text{C}; D=0; \text{ parameter: } t_p$$

Diagram 4: Typ. output characteristics



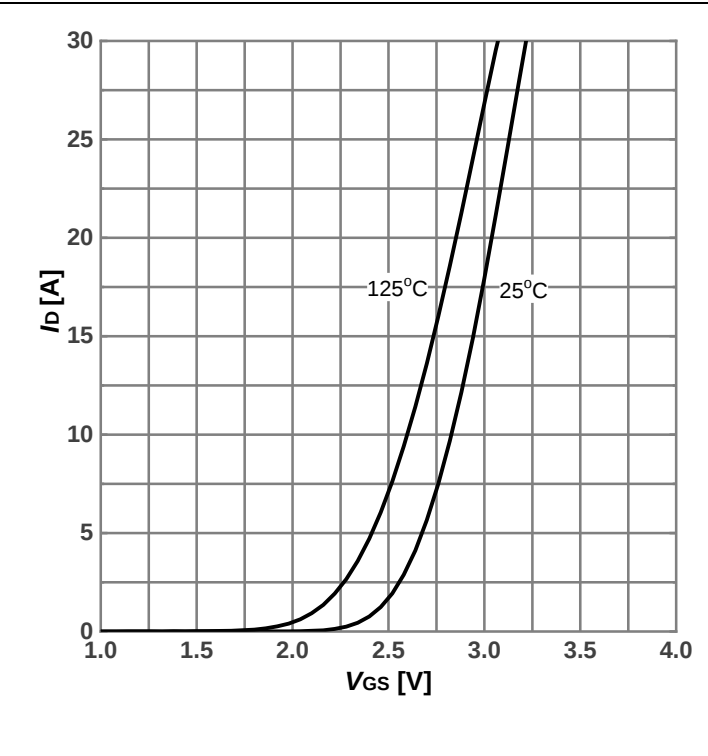
$$I_D=f(V_{DS}); T_J=25^{\circ}\text{C}; \text{ parameter: } V_{GS}$$

Diagram 5: Typ. output characteristics



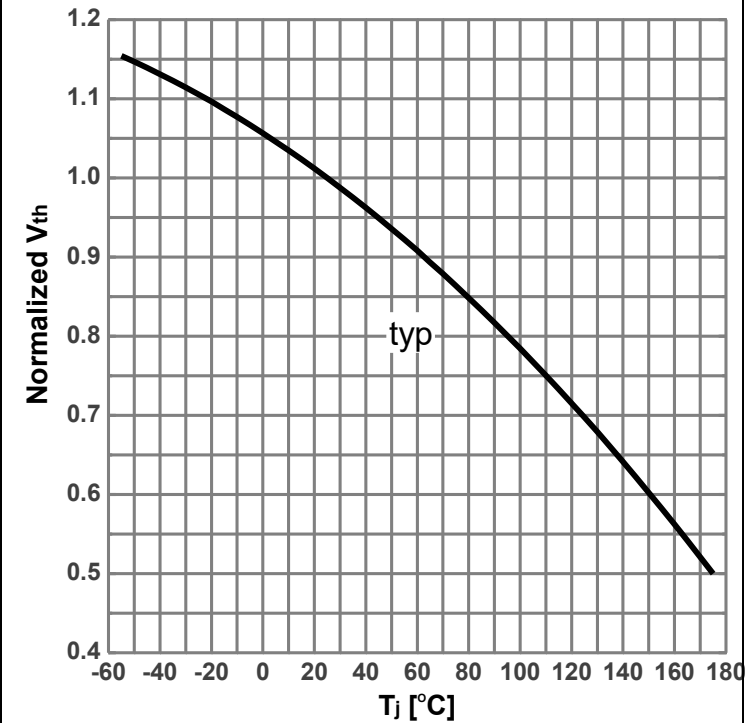
$I_D=f(V_{DS})$; $T_j=125^{\circ}\text{C}$; parameter: V_{GS}

Diagram 6: Typ. transfer characteristics



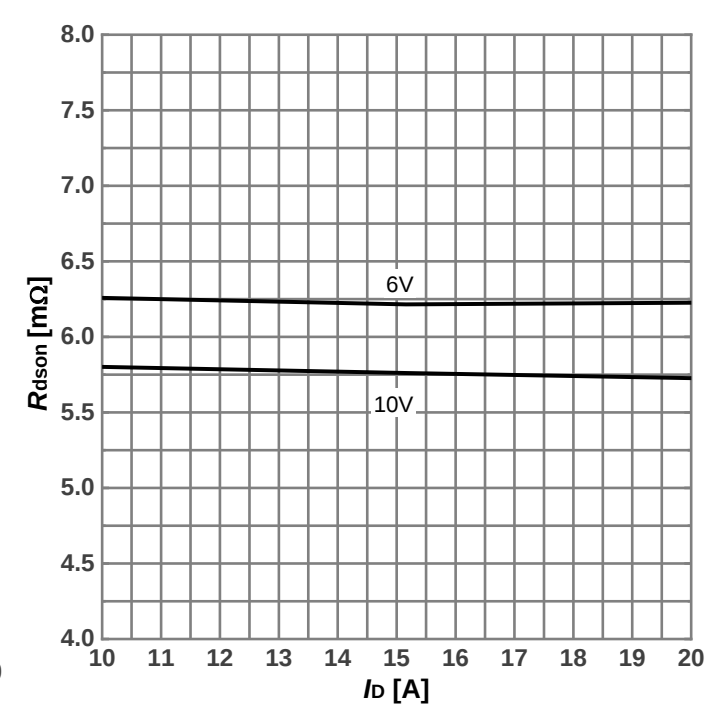
$I_D=f(V_{GS})$; $V_{DS}=5\text{V}$; parameter: T_j

Diagram 7: Gate threshold voltage vs. Junction temperature

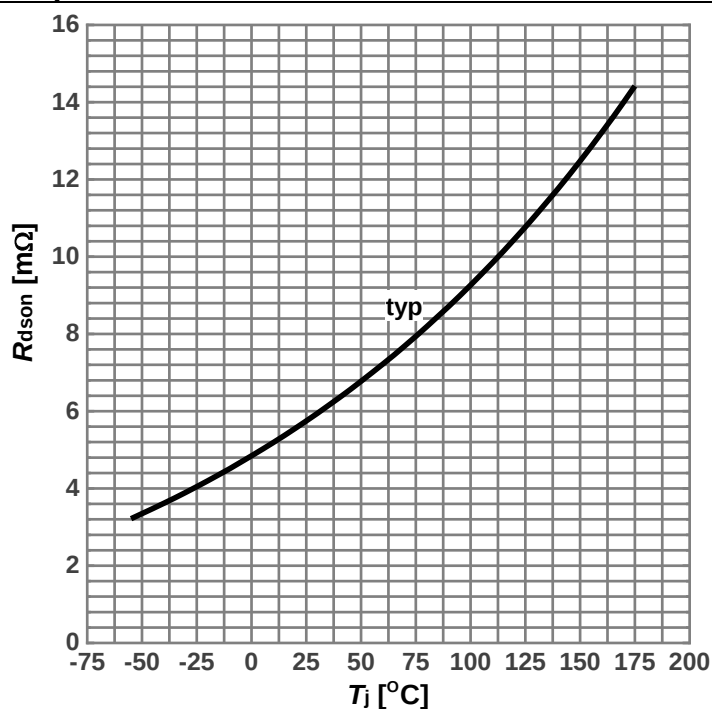


$V_{th}=f(T_j)$; $I_D=250\mu\text{A}$

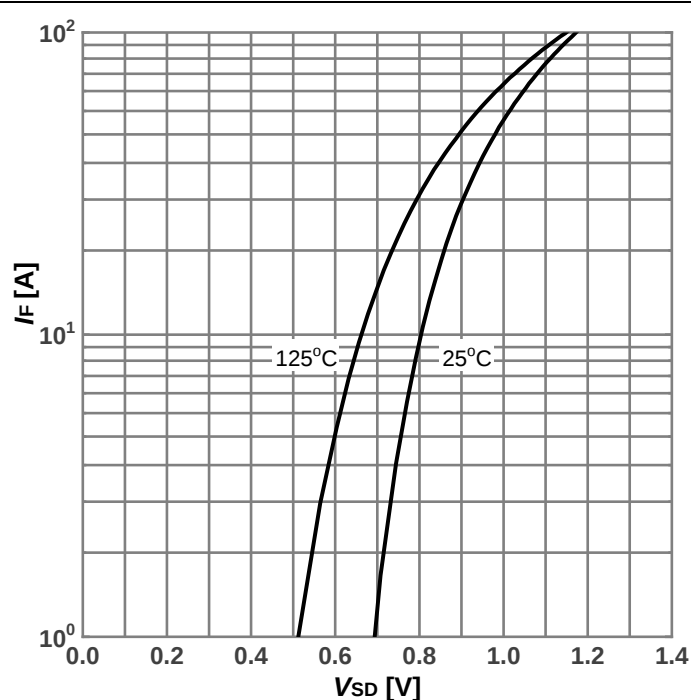
Diagram 8: On-state resistance vs. Drain current



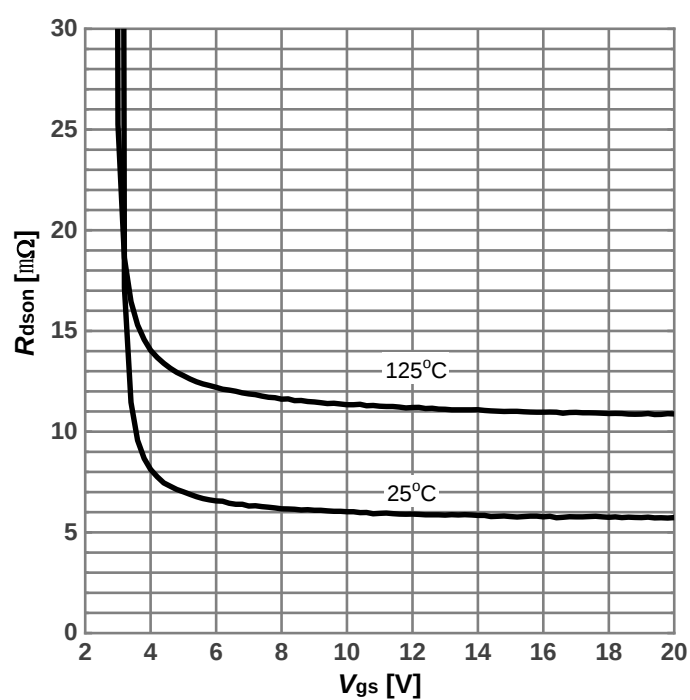
$R_{DS(on)}=f(I_D)$; $T_j=25^{\circ}\text{C}$; parameter: V_{GS}

Diagram 9: On-state resistance vs. Junction temperature

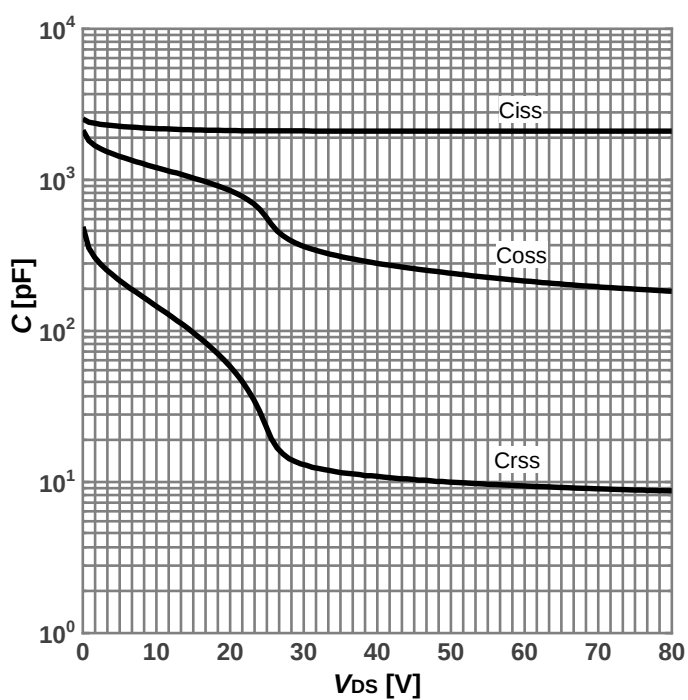
$$R_{DS(on)}=f(T_j); I_D=20A; V_{GS}=10V$$

Diagram 10: Forward characteristics of reverse diode

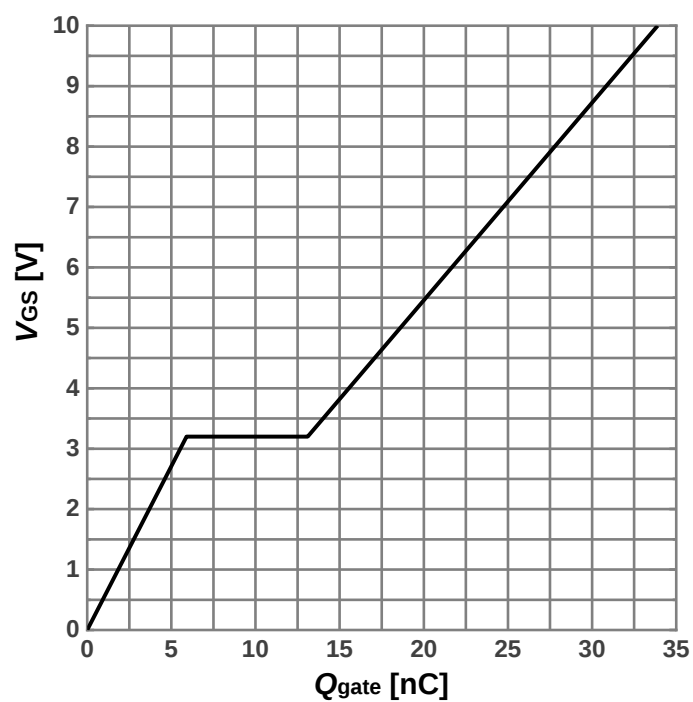
$$I_F=f(V_{SD}); \text{parameter: } T_j$$

Diagram 11: On-state resistance vs. Vgs characteristics

$$R_{DS(on)}=f(V_{GS}); I_D=20A$$

Diagram 12: Typ. capacitances

$$C=f(V_{DS}); V_{GS}=0V; f=250kHz$$

Diagram 13: Typ. gate charge

$V_{GS}=f(Q_{gate})$; $I_D=20A$ pulsed; $V_{DS}=40V$

6. Test Circuits

Table 7. Diode Characteristics

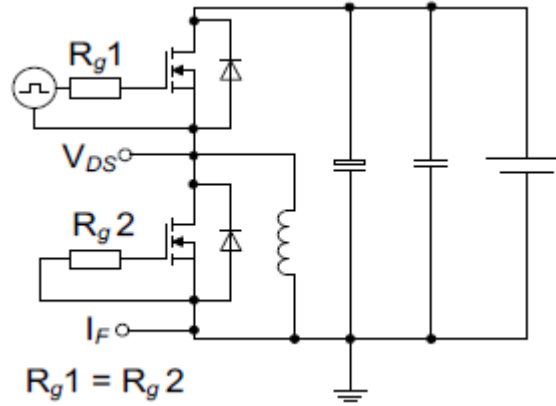
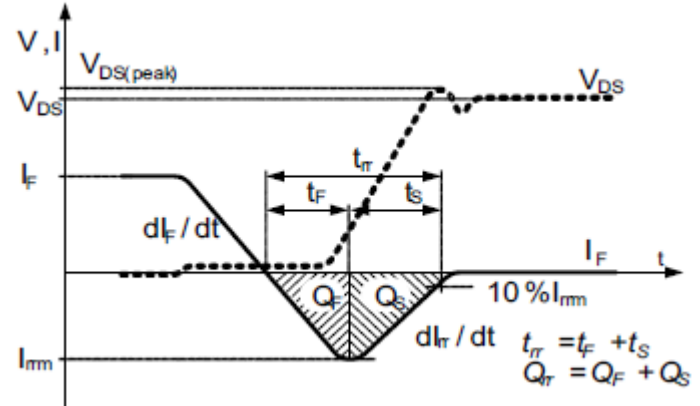
Test circuit for diode characteristics	Diode recovery waveform
 $R_{g1} = R_{g2}$	 $V_{DS(peak)}$ V_{DS} I_F dI_F/dt t_F t_{rr} t_S $10\% I_{rm}$ I_{rm} dI_{rr}/dt $t_{rr} = t_F + t_S$ $Q_{rr} = Q_F + Q_S$

Table 8. Switching Times

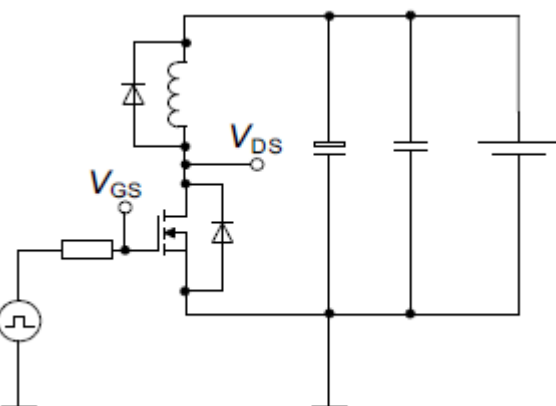
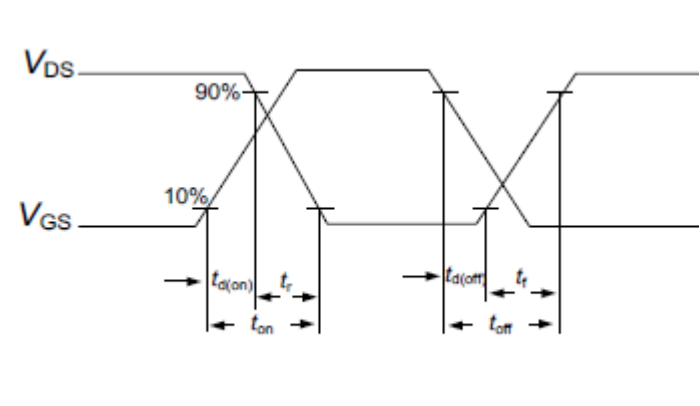
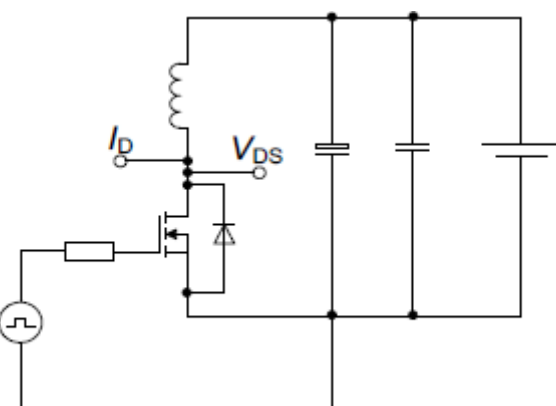
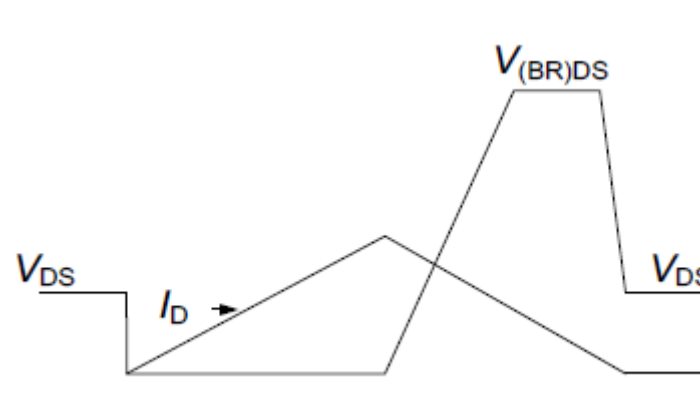
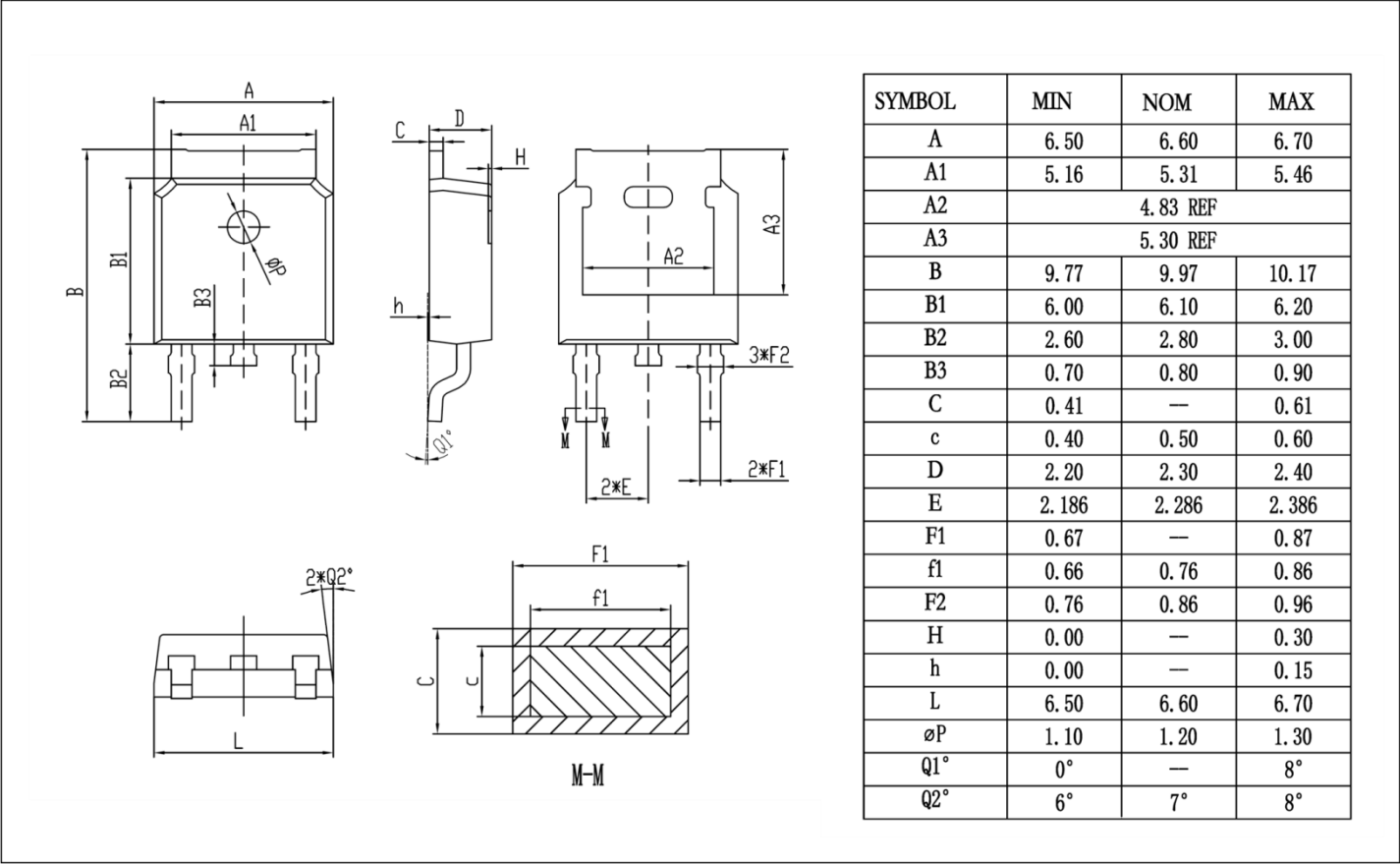
Switching times test circuit for inductive load	Switching times waveform
	 V_{DS} 90% 10% V_{GS} $t_{d(on)}$ t_r t_{on} $t_{d(off)}$ t_r t_{off}

Table 9. Unclamped Inductive Load

Unclamped inductive load test circuit	Unclamped inductive waveform
	 $V_{(BR)DS}$ V_{DS} I_D

7. Package Outlines

Figure 1 Outline TO-252 Dimensions in mm



8. Appendix

CoolSemi Webpage: www.coolsemi.com.